

Radiation effects on microelectronics: overview, design and testing guidelines, and Frontgrade Gaisler case examples

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Radiation Effects Section Head



Radiation-hard electronics – challenges,
design strategies and measurements
29 January 2026, Online

Agenda



- | | | | |
|-----------|--|-----------|------------------------------|
| 01 | Introduction | 04 | Radiation effects mitigation |
| 02 | Space radiation environment | 05 | Radiation hardness assurance |
| 03 | Radiation effects on electronic components | 06 | Conclusions |

01



Introduction



Established 2001 as a spin-off from
Chalmers and European Space Agency



Located in Gothenburg, Sweden
75+ employees in Sweden, Germany,
France, Spain, and United Kingdom




Experts in fault-tolerant computing




Focused mainly on
radiation hardened microprocessors






 World leader in radiation hardened space components (top three in the world) with a unique connection to ESA, EU, and NASA.

 Operating as a fab-less component supplier with manufacturing outsourced to foundries, assembly and test in Europe. In-house facilities for advanced hardware and software design.

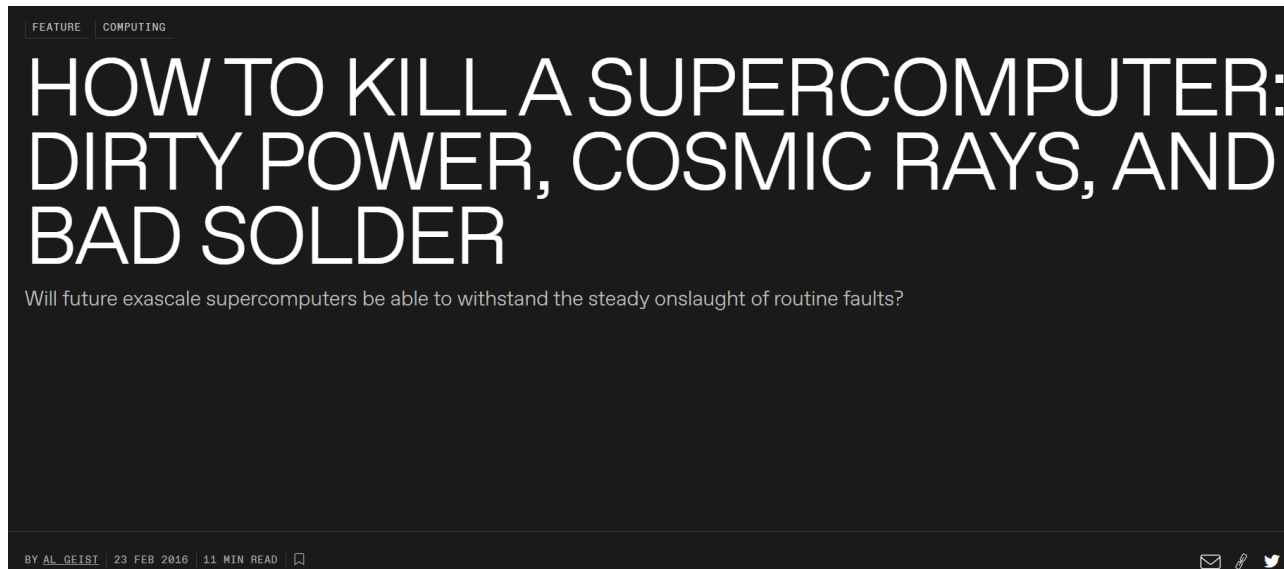
 Customers – Airbus, Thales Group, Beyond Gravity, Lockheed Martin, Northrop Grumman, Boeing, L3Harris, Raytheon, Mitsubishi, ULA, and others.

 Applications – GPS III, Galileo, Copernicus, SDA Tranche 0, OneWeb, IridiumNEXT, Ariane 6, H3, Vulcan, Vega, ...

Introduction

Some context on radiation effects on electronic components... **Ground**

Supercomputers case(s)



<https://spectrum.ieee.org/how-to-kill-a-supercomputer-dirty-power-cosmic-rays-and-bad-solder>

Jaguar (2009 #1 Top 500 list):

“Just how many spurious bit flips are happening inside supercomputers already? To try to find out, researchers performed a study in 2009 and 2010 on the then most powerful supercomputer—a Cray XT5 system at Oak Ridge, in Tennessee, called Jaguar.

Jaguar had 360 terabytes of main memory, all protected by ECC. I and others at the lab set it up to log every time a bit was flipped incorrectly in main memory. When I asked my computing colleagues elsewhere to guess how often Jaguar saw such a bit spontaneously change state, the typical estimate was about a hundred times a day. In fact, Jaguar was logging ECC errors at a rate of 350 per minute.

In addition to the common case of a single cosmic ray flipping a single bit, in some cases a single high-energy particle cascaded through the memory chip flipping multiple bits. And in a few cases the particle had enough energy to permanently damage a memory location.”

ECC = Error-Correcting Code

Introduction

Some context on radiation effects on electronic components... **Ground**

Toyota case

Toyota Problems Caused By Cosmic Rays? ›NHTSA Supposedly Checking It Out

BY ROBERT N. CHARETTE | 16 MAR 2010 | 1 MIN READ | 

Robert N. Charette is a Contributing Editor and an acknowledged international authority on information technology and systems risk management.

<https://spectrum.ieee.org/toyota-problems-caused-by-cosmic-rays>

"The Detroit Free Press has a story today that claims the US National Highway Traffic Safety Administration (NHTSA) is investigating whether cosmic rays are the cause of Toyota's sudden acceleration problems.

According to the story, an anonymous tipster last month wrote NHTSA hypothesizing that, "It is possible that Toyota is using electronic parts that are more susceptible to SEUs [Single Event Upsets] than other manufacturers. Components such as RAM, DRAM, SRAM, FGPAs, ASICs, etc... can all be susceptible."

The tipster says that, "The automotive industry has yet to fully embrace fault-tolerant architectures and software development methods that are used widely by the avionics industry," and that the chips used by Toyota may not be hardened against interference."

Introduction

Some context on radiation effects on electronic components... **Aviation**

Airbus case

AIRBUS

Press Release

Airbus update on A320 Family precautionary fleet action

Toulouse, France, **28 November 2025** – Analysis of a recent event involving an A320 Family aircraft has revealed that intense solar radiation may corrupt data critical to the functioning of flight controls.

Airbus has consequently identified a significant number of A320 Family aircraft currently in-service which may be impacted.

Airbus has worked proactively with the aviation authorities to request immediate precautionary action from operators via an Alert Operators Transmission (AOT) in order to implement the available software and/or hardware protection, and ensure the fleet is safe to fly. This AOT will be reflected in an Emergency Airworthiness Directive from the European Union Aviation Safety Agency (EASA).

Airbus acknowledges these recommendations will lead to operational disruptions to passengers and customers. We apologise for the inconvenience caused and will work closely with operators, while keeping safety as our number one and overriding priority.

<https://www.airbus.com/en/newsroom/press-releases/2025-11-airbus-update-on-a320-family-precautionary-fleet-action>

Introduction

Some context on radiation effects on electronic components... **Space**

SpaceX Crew Dragon 2021 case



Fire, Fire

The SpaceX Crew Dragon dubbed Resilience, currently docked to the International Space Station after launching in November of last year, just reportedly scared the bejesus out of the station's crew.

The capsule "annunciated false emergency messages for Fire and Rapid Depress as well as other erroneous messages yesterday," *NASASpaceFlight* managing editor Chris Bergin reported in a [Thursday afternoon tweet](#). "ISS crew ran responses for Fire and Rapid depress but stood down once stable readings were confirmed."

<https://futurism.com/the-byte/emergency-alarm-spacex-dragon-space-station>

According to Bergin, the ISS reported that the issue was likely a "Single Event Upset" on one of the Crew Dragon's power units, causing a processor to reset "and output data which the ISS interpreted as a collection of emergencies and off-nominal indications."

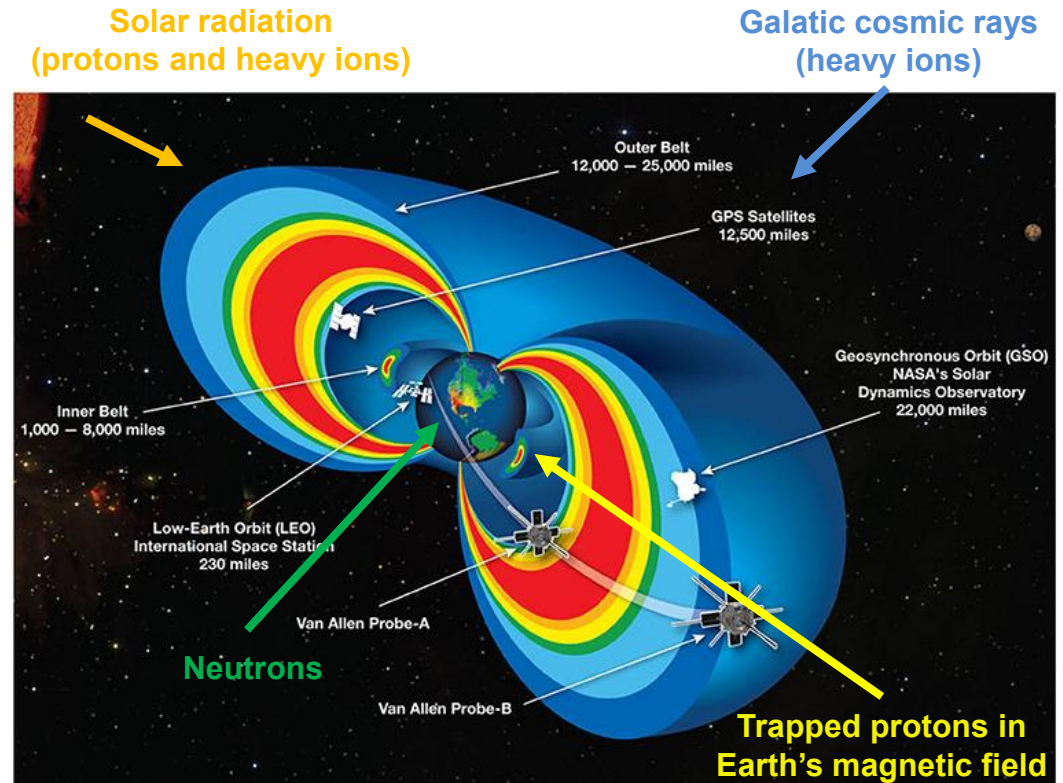
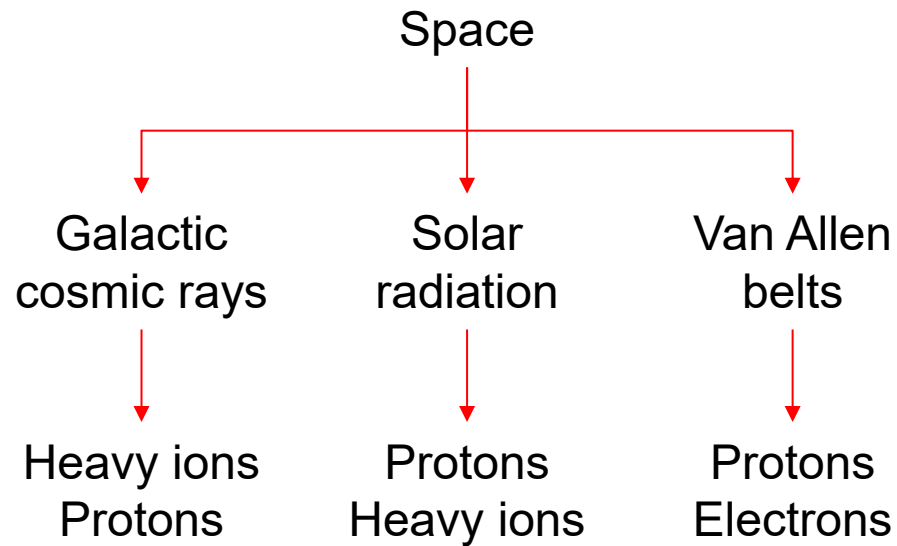
02



Space radiation environment

Space radiation environment

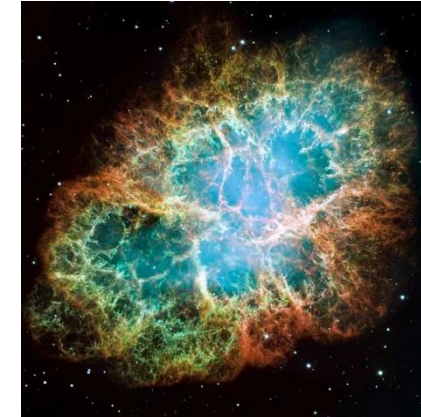
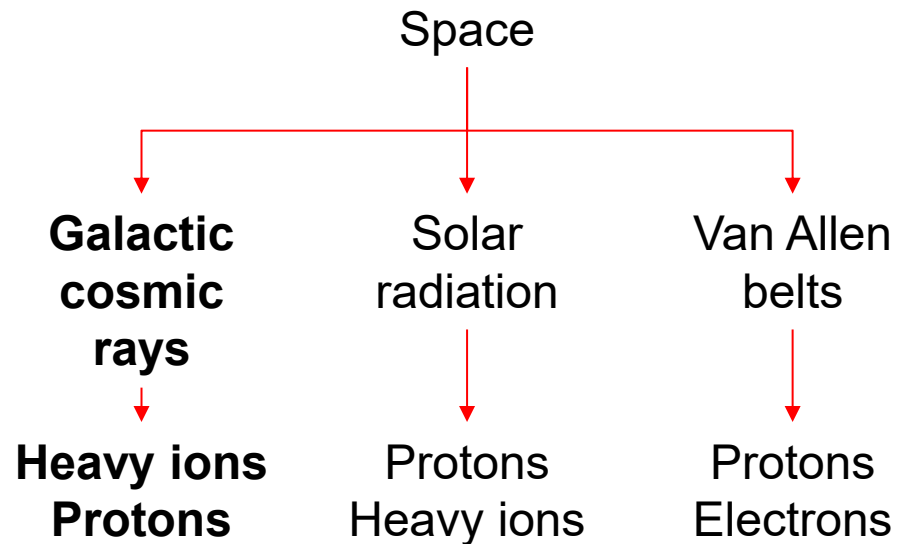
Radiation sources



Credit: NASA.

Space radiation environment

Radiation sources



Credit: NASA.

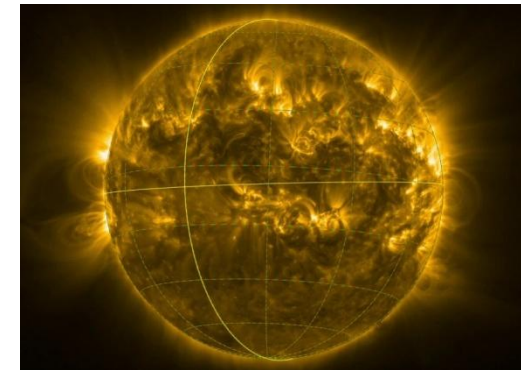
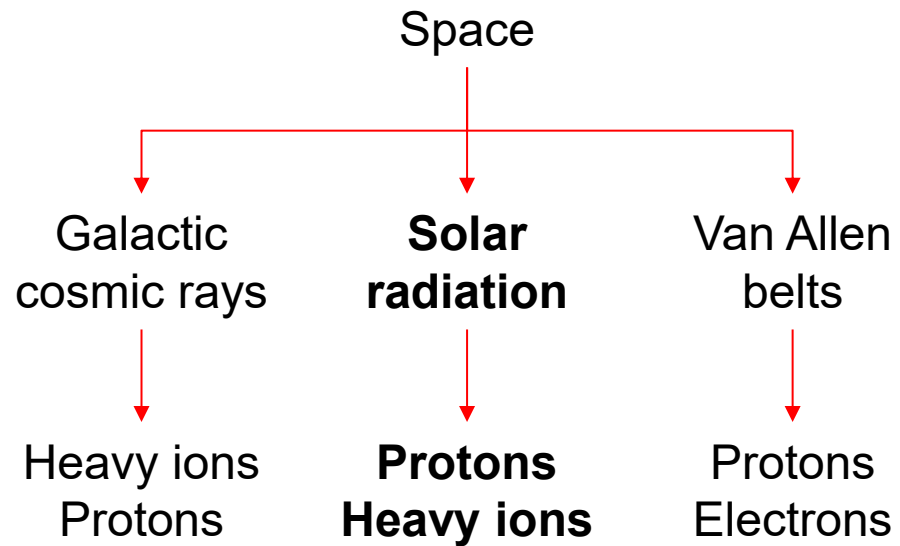
Typically found in free space
(outside the Earth's magnetic field).

Originated outside our solar system by:

- Supernova explosions.
- Celestial body collisions.
- Other major events.

Space radiation environment

Radiation sources



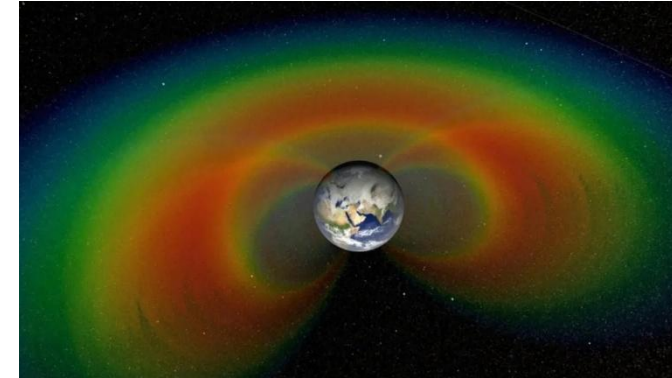
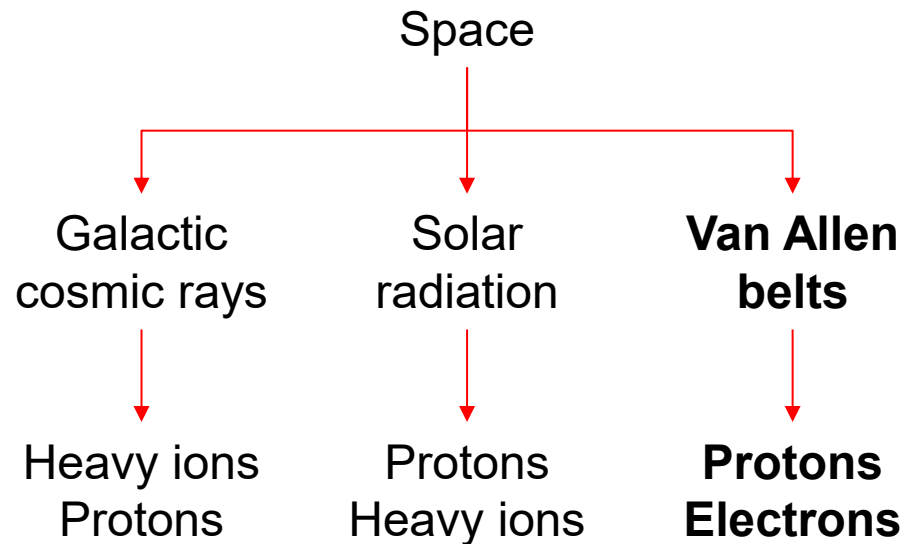
Credit: ESA.

Generated by the solar activity:

- Solar wind.
- Solar flares.
- Coronal mass ejections.

Space radiation environment

Radiation sources



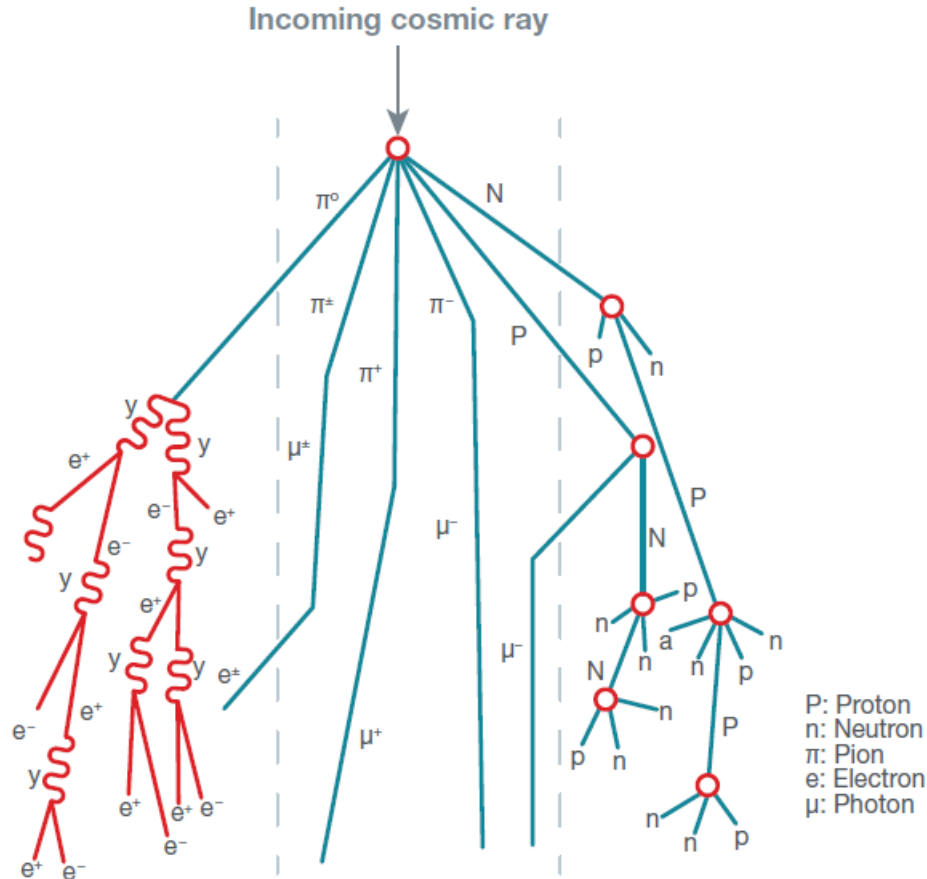
Credit: NASA.

Radiation belts can form around any planetary body that has a magnetic field (magnetosphere) of sufficient strength to divert and capture particles before they can enter the planet's atmosphere.

The Earth's magnetic field collects and traps protons and electrons, creating doughnut-shaped (toroidal) concentrated regions of trapped charged particles in the vicinity of Earth.

Space radiation environment

Terrestrial radiation environment



Credit: Texas Instruments.

Coulombic interactions in the upper atmosphere quickly stop heavier ions (and alpha particles), leaving only the high-energy protons to react in the upper atmosphere.

The protons undergo nuclear reactions via strong force, with oxygen and nitrogen nuclei producing huge and complex *cascades of “secondary” particles that shower down through the atmosphere to the Earth’s surface.*

The *predominant particle fluxes at sea level include muons, protons, electrons, neutrons and pions.* Due to their relatively high flux and stability, the neutrons are the most likely cosmic radiation to induce effects in devices at terrestrial altitudes.

13 n/(cm²·h) @ sea level, according to JEDEC JESD89A.

The neutron flux increases with altitude, being hundreds of times higher at commercial flight altitudes.

Space radiation environment

Summary of environmental hazards

		Environment		
		LEO Equatorial	LEO Polar (Sun Sync)	GEO / Interplanetary
Mission Lifetime	> 3 Years	Moderate Dose / Attenuated GCR, Trapped Proton, SAA, Some Solar Proton dependence for variation	High Dose / Higher GCR, High Energy Trapped Protons in SAA and Poles, Some Solar Proton dependence for variation	High Dose / High GCR, High Solar Proton Variability
	1-3 Years	Manageable Dose / Attenuated GCR, Trapped Proton, SAA, Some Solar Proton dependence for variation	Moderate Dose / Higher GCR, High Energy Trapped Protons in SAA and Poles, Some Solar Proton dependence for variation	High Dose / High GCR, High Solar Proton Variability
	< 1 Year	Manageable Dose / Attenuated GCR, Trapped Proton, SAA, Some Solar Proton dependence for variation	Moderate Dose / Higher GCR, High Energy Trapped Protons in SAA and Poles, Some Solar Proton dependence for variation	Moderate Dose / High GCR, High Solar Proton Variability

Credit: NASA.

Degradation has a strong dependence not only on where you go, but also how long you stay on orbit.

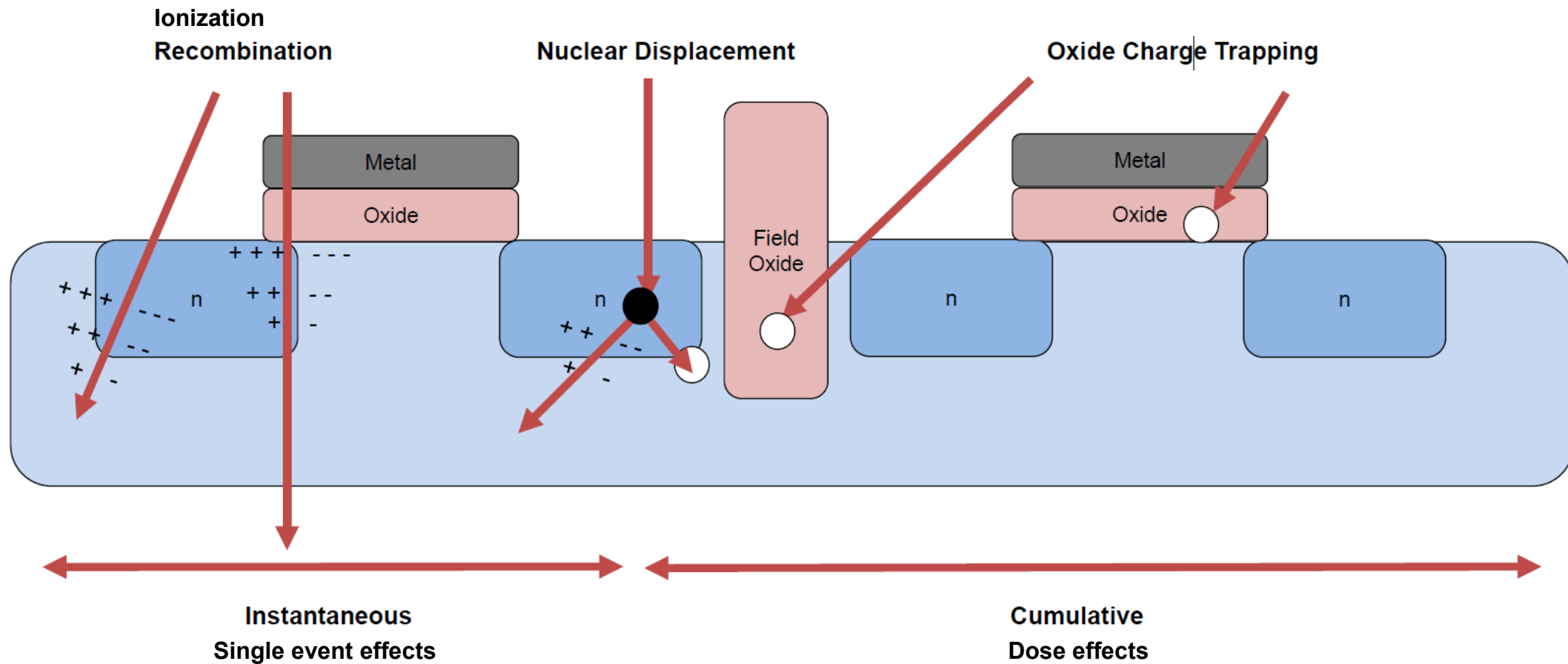
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Radiation effects on electronic components

Radiation effects on electronic components

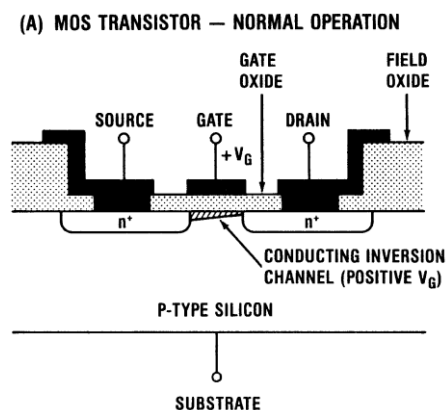
Particle and device interaction



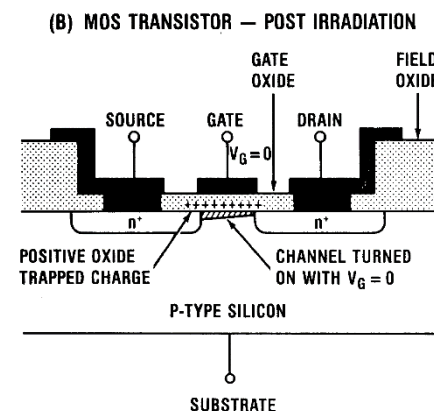
Radiation effects on electronic components

Dose effects – Total Ionizing Dose (TID)

Dose effects are characterized by *lasting parametric shifts that accumulate over time* due to chronic radiation exposure (a large number of radiation events), ultimately leading the semiconductor device to drift out of tolerance and eventually fail.



Applying adequate voltage on gate creates a conducting channel between the source and the drain: the device is ON!



Due to ionizing radiation, the charges trapped in gate oxide cause a shift in the threshold voltage necessary to turn device ON.

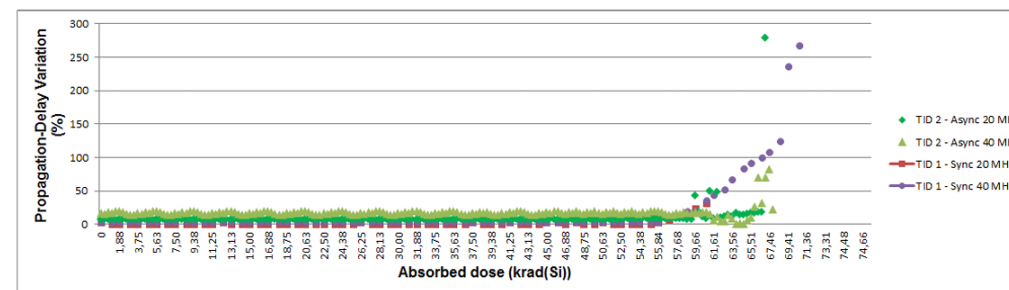
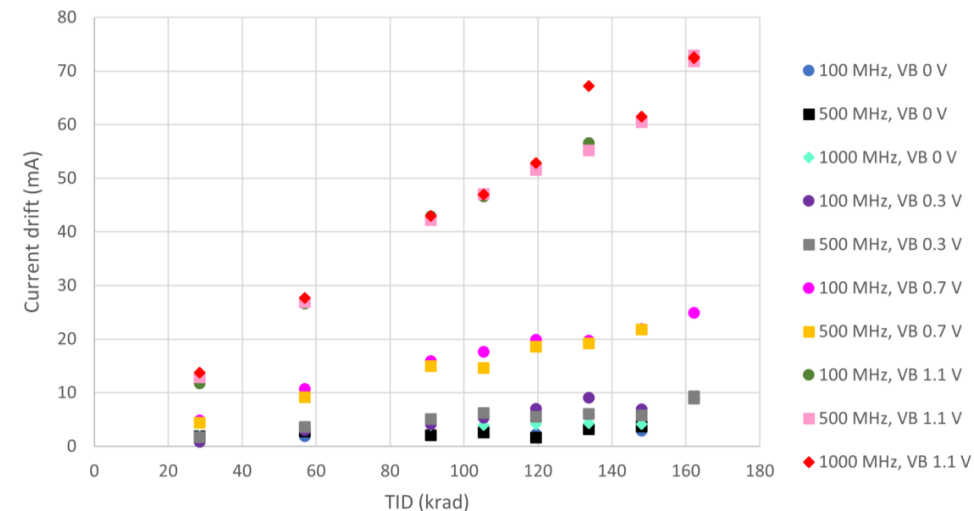
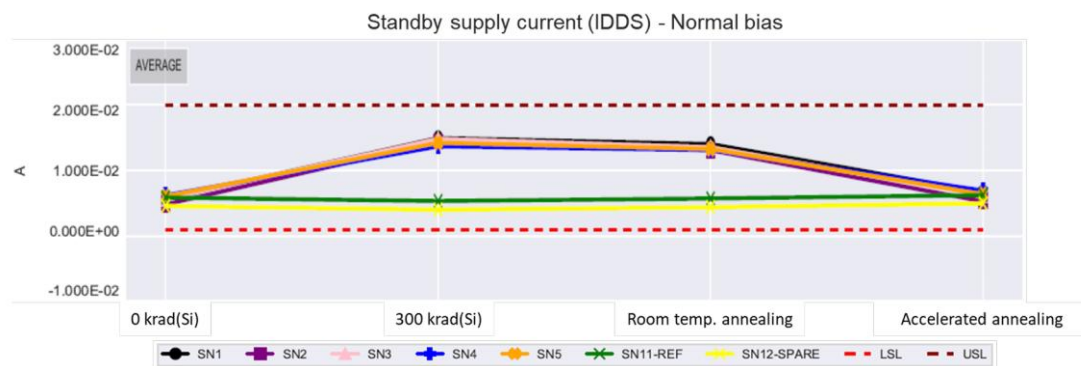
If the shift significant enough, then the transistor cannot be turned OFF even at gate voltage = 0V.

Radiation effects on electronic components

Dose effects – Total Ionizing Dose (TID)

Unit:

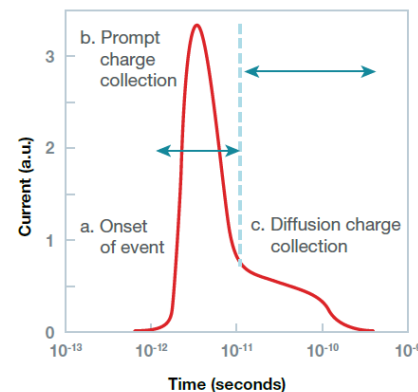
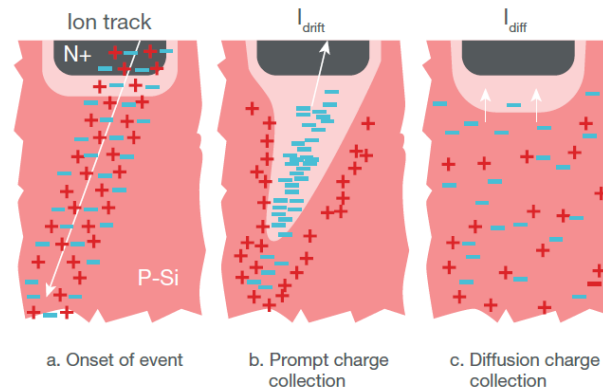
- Radiation absorbed dose: rad(Si)
 - 1 rad = 100 erg/g = 0.01 J/kg.
 - 100 rad = 1 Gy.
- This is not exposure (R), or dose equivalent (Sv).



Radiation effects on electronic components

Single Event Effect (SEE)

SEEs are *random, instantaneous disruptions triggered by the passage of a single energetic particle*. One radiation event equals one upset occurrence. An upset could lead to failures in more than one device or bit for each individual radiation event.



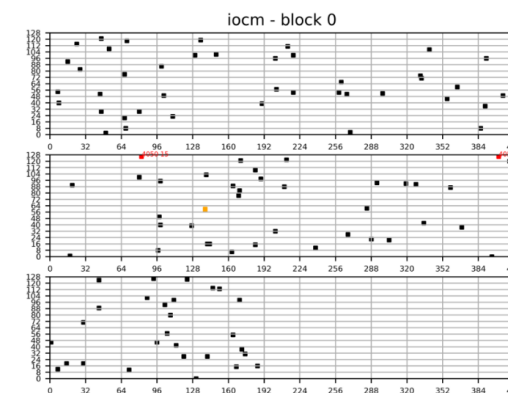
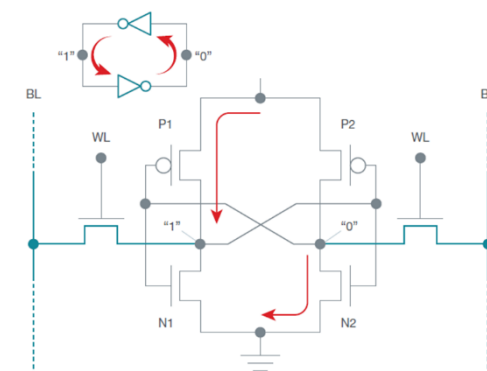
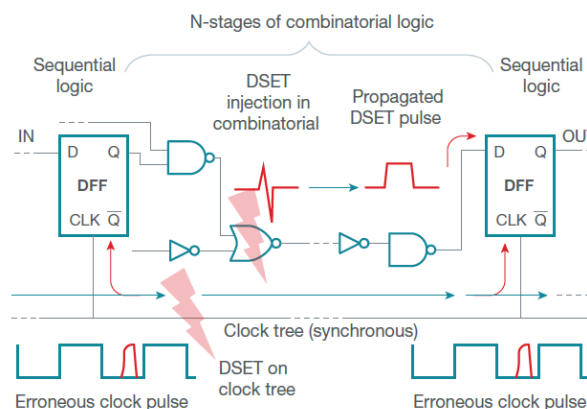
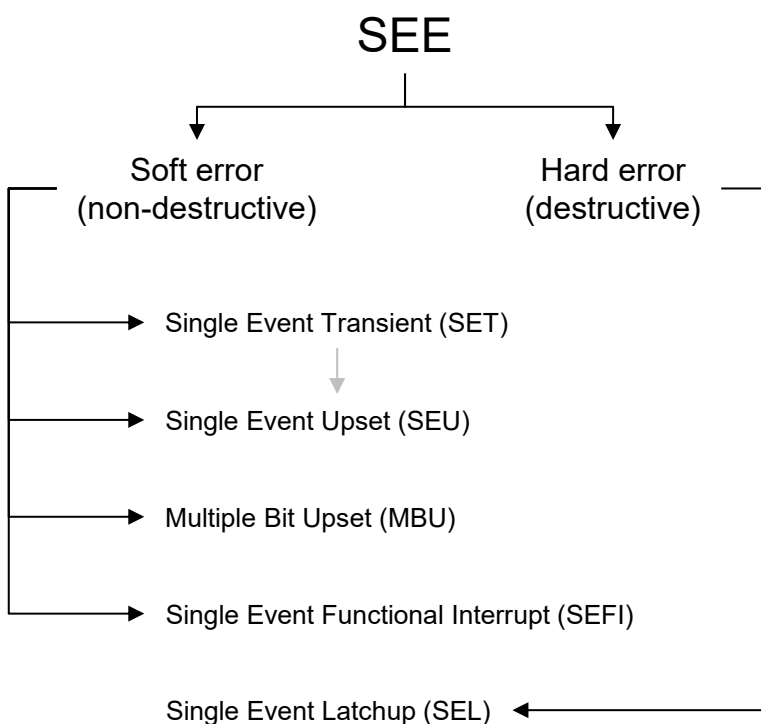
Units:

- Heavy ions:
 - Linear Energy Transfer (LET), MeV·cm²/mg.
 - Stopping power normalized to target material.
- Protons:
 - Energy, MeV.
- Cross section (σ):
 - Device-particle interaction (cm²).
 - Used in calculation of rate.
 - Can be /device or /bit.

Radiation effects on electronic components

Single Event Effect (SEE)

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04

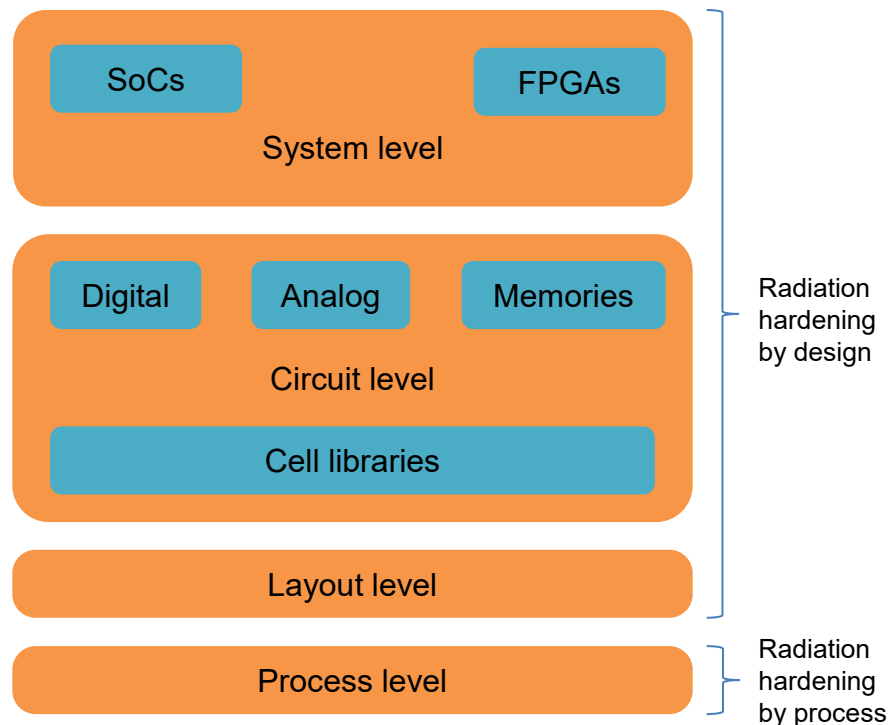


Radiation effects mitigation

Radiation effects mitigation

Overview

Different mitigation techniques can be applied at different abstraction levels and stages of the development of a radiation-hardened component.



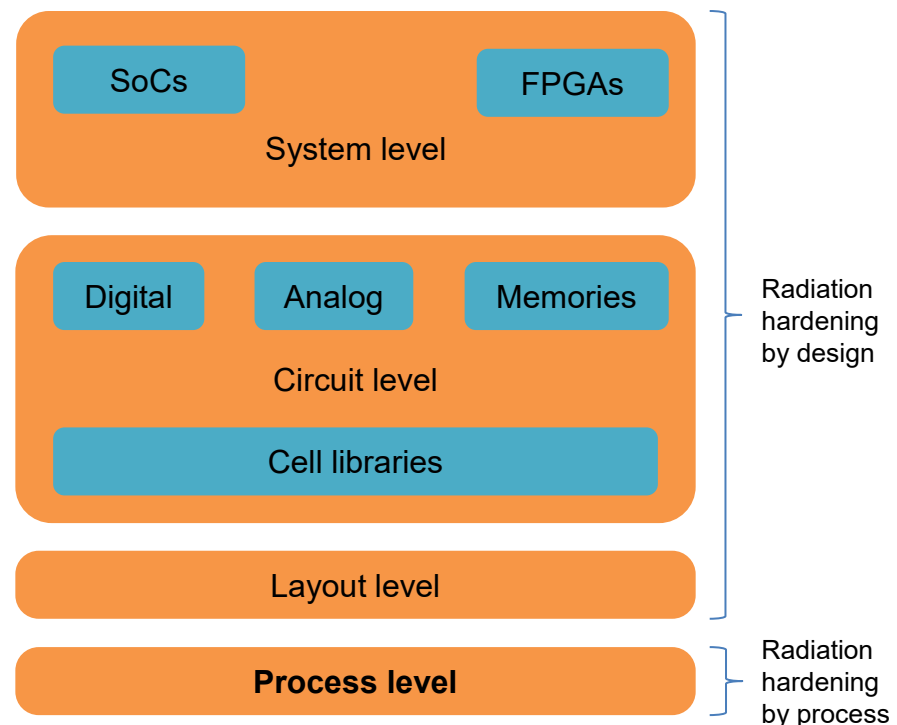
Radiation effects mitigation

Overview

Different mitigation techniques can be applied at different abstraction levels and stages of the development of a radiation-hardened component.

Process:

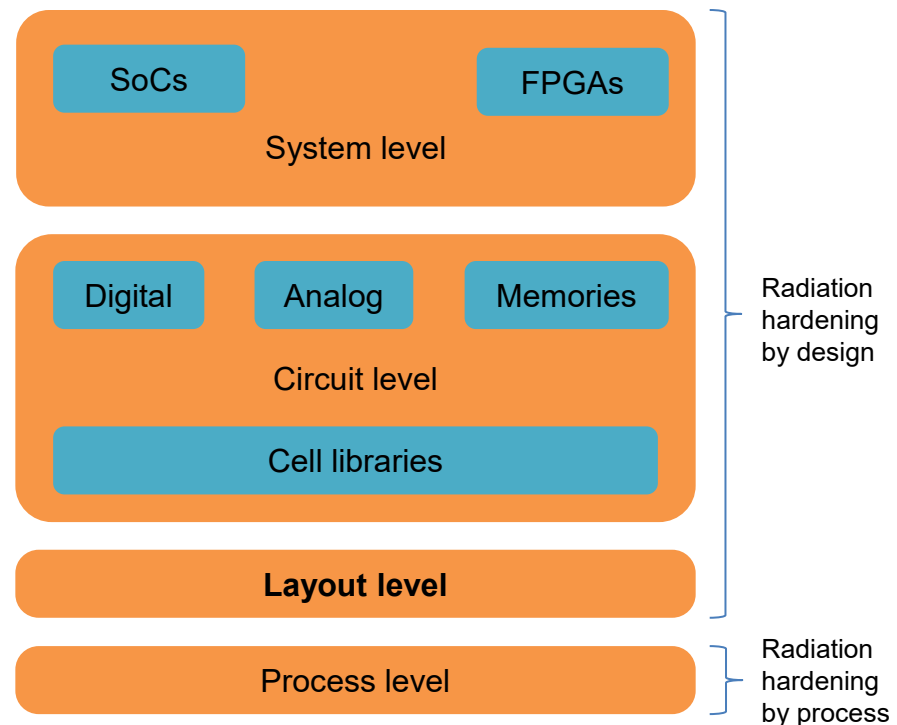
- Modification of existing semiconductor's manufacturing processes to cope with radiation effects.



Radiation effects mitigation

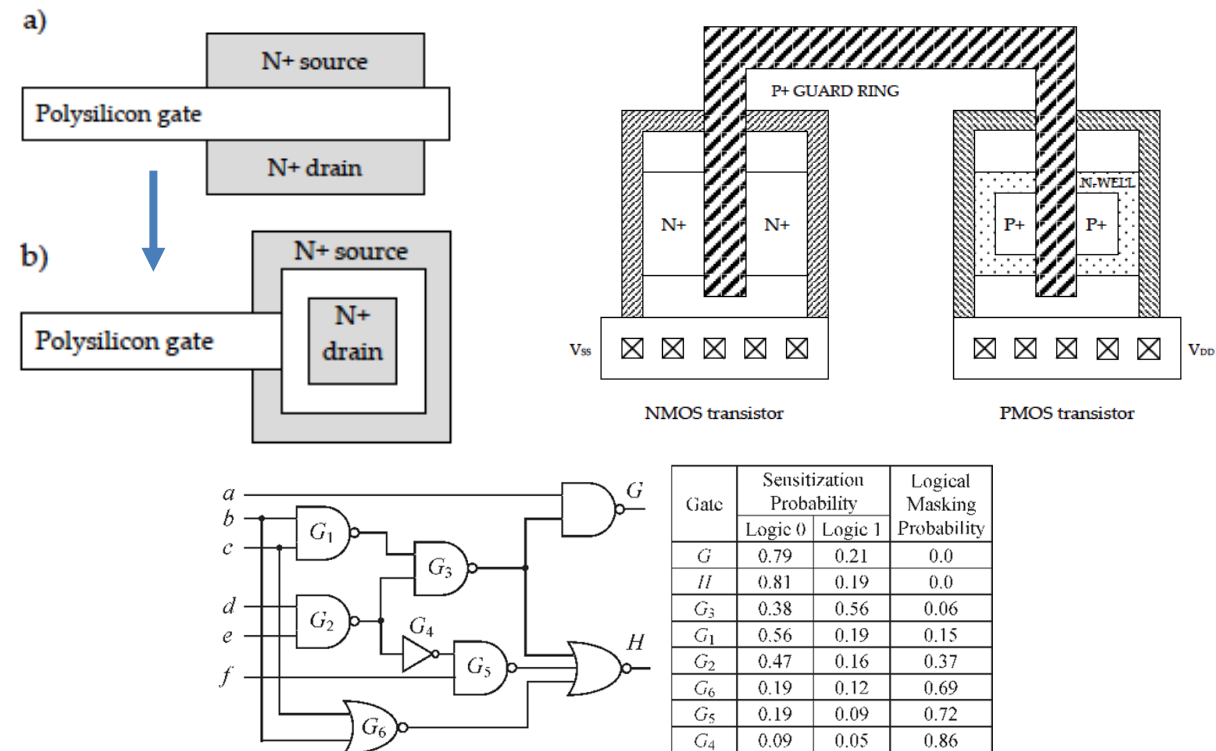
Overview

Different mitigation techniques can be applied at different abstraction levels and stages of the development of a radiation-hardened component.



Layout:

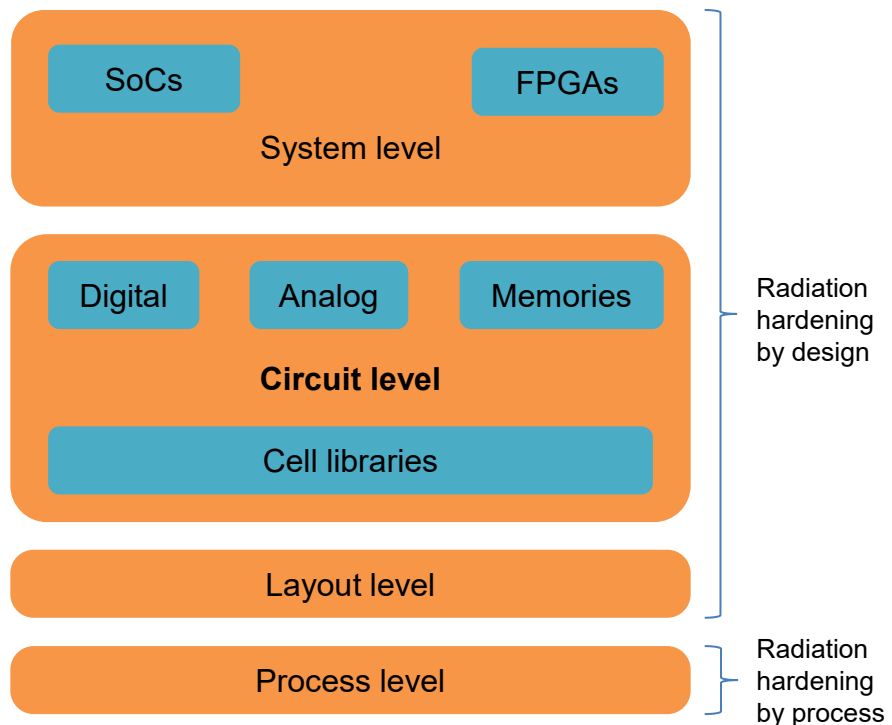
- Modification of the transistor's shapes and insertion of protection elements to reduce mainly the effects of TID and SEL but also SET and SEU.



Radiation effects mitigation

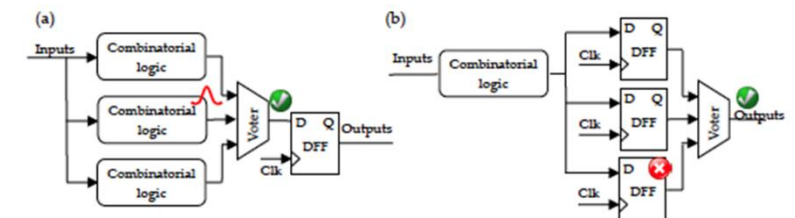
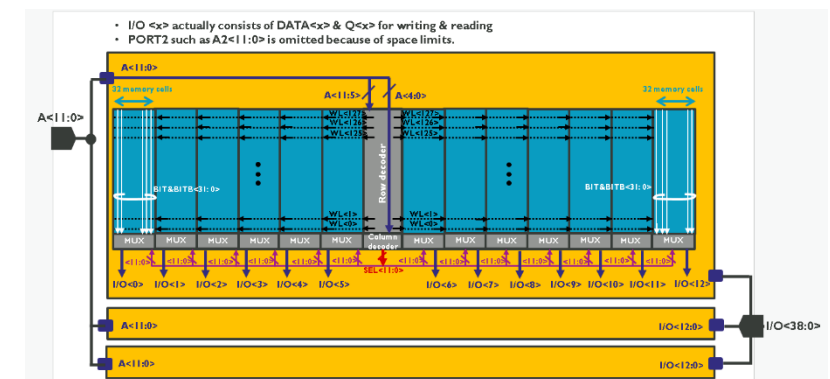
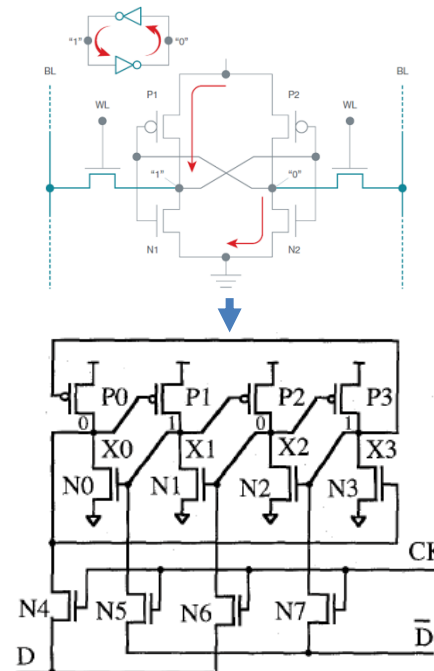
Overview

Different mitigation techniques can be applied at different abstraction levels and stages of the development of a radiation-hardened component.



Circuit level:

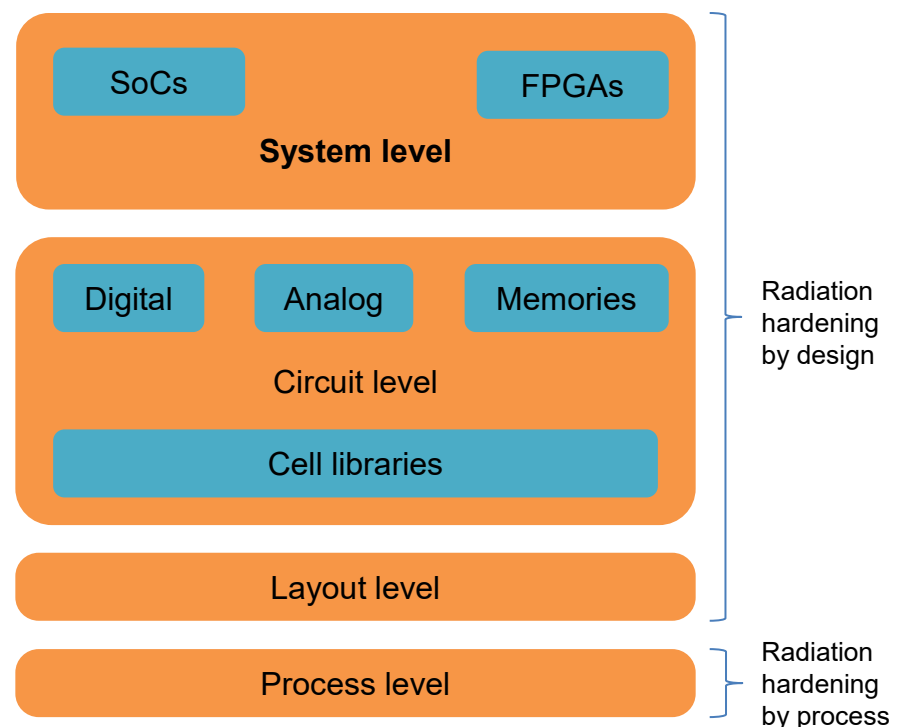
- Hardening of basic functional cells and then manufacture in commercial ASIC processes.
- Hardening a library consists of combining several other techniques at process, layout, analog, digital, and memory levels.



Radiation effects mitigation

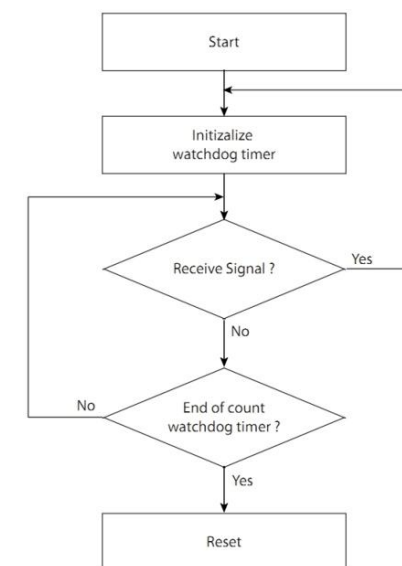
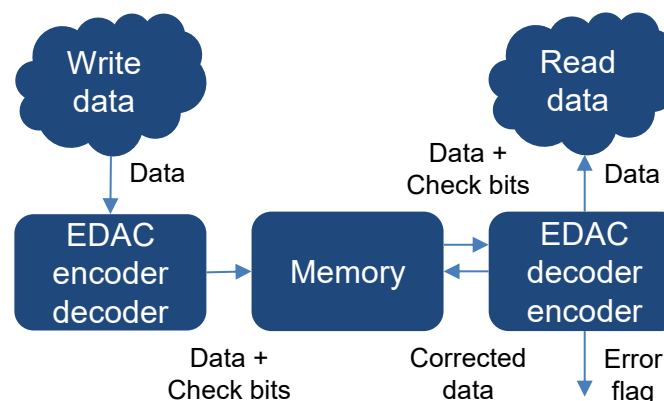
Overview

Different mitigation techniques can be applied at different abstraction levels and stages of the development of a radiation-hardened component.



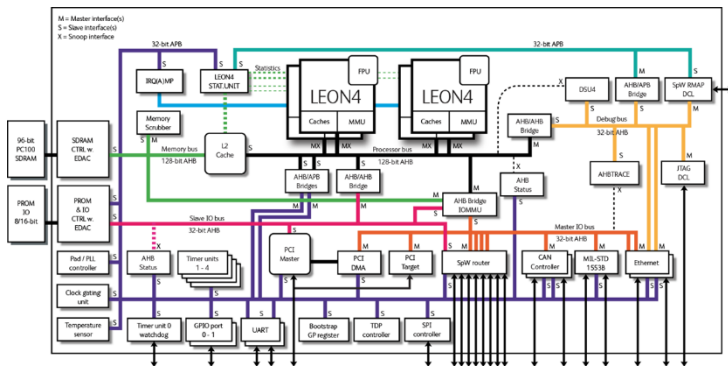
System level:

- Techniques applied to different cores (hard or soft) within a device .
- Several of them used in conjunction with lower-level techniques, such as memories.
- Needed to meet the radiation tolerance required.



Radiation effects mitigation

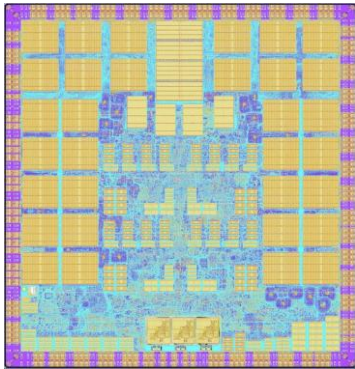
Example – GR740 – Rad-Hard Quad-Core LEON4FT System-on-Chip



SEE

Environment	Events/device/day	Mean time between events (years)
GEO	7.81E-6	350
LEO	2.09E-6	1310

TID 300 krad(Si)



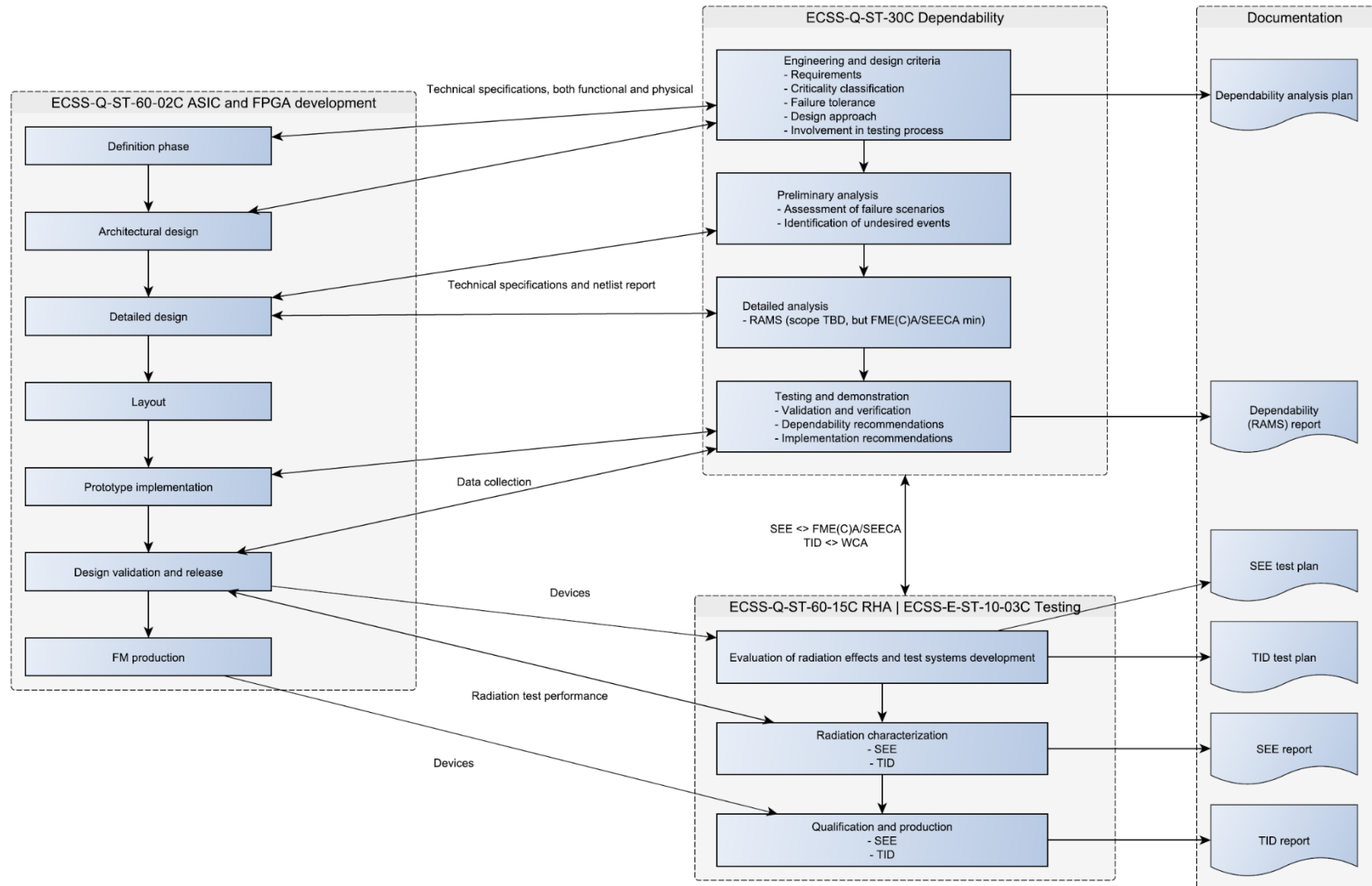
- Processor cores in the GR740 have register files containing CORELIB flip-flops (C65SPACE, non-SEU hardened).
 - Block TMR with bit-by-bit voting on the register read data outputs is implemented in the register files to mask SEUs.
 - Modules of the BTMR have adequate spacing among them to avoid sensitivity to potential uncorrectable MBUs.
- L1 cache of each processor core is composed of SRAM cells and includes an 8+1 parity error detection system with invalidation on error scheme.
- L2 cache is also composed of SRAM cells and includes a 32+7 BCH SECDED scheme.
 - Scrambling of all memory cells, one bit every four from the same word, is used to minimize the possibility of MBUs within one word.
- SpaceWire and the Ethernet core also include memory blocks implemented with SRAM cells.
 - Protected either with TMR or PDMR (Parity DMR).
- All other memory cells and sequential logic in the GR740 are composed of SKYROB flip-flops (C65SPACE, SEU hardened) that do not require additional mitigation at design level thanks to its RHBD approach at cell library level (C65SPACE).
- Three RHBD PLLs are used in the GR740 and all global clocks and reset networks are SET hardened at cell library level (C65SPACE).

05



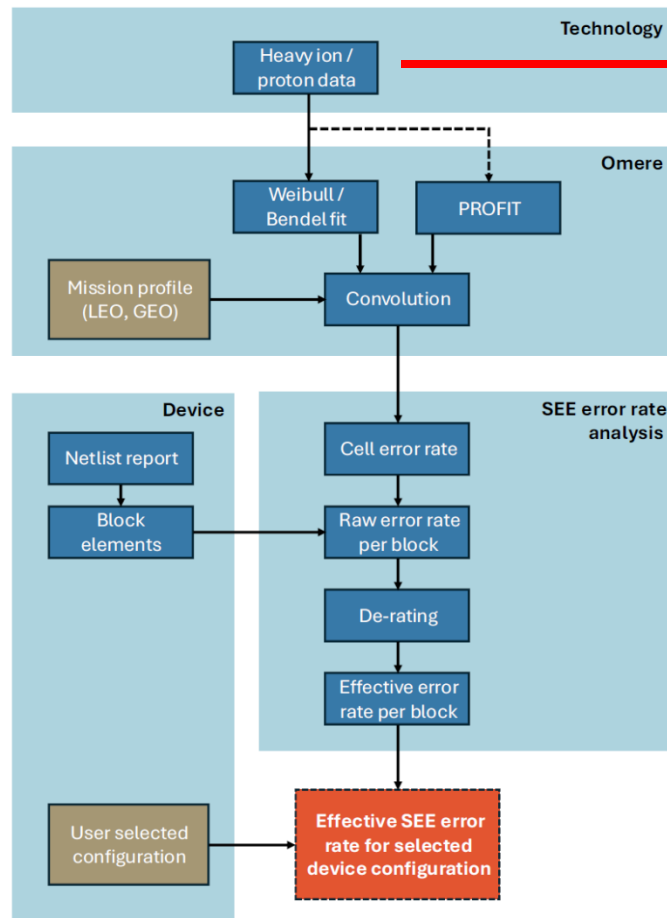
Radiation Hardness Assurance (RHA)

Radiation hardness assurance | Life cycle



Radiation hardness assurance | Analysis

How do we estimate the radiation performance of a device during its design phase?

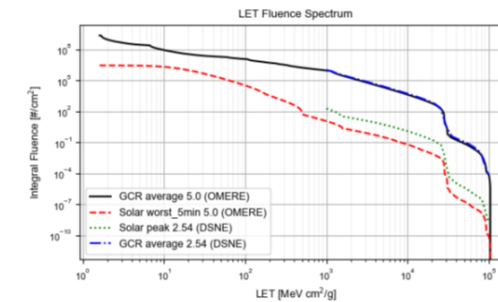
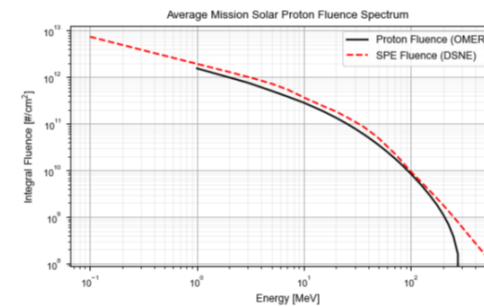
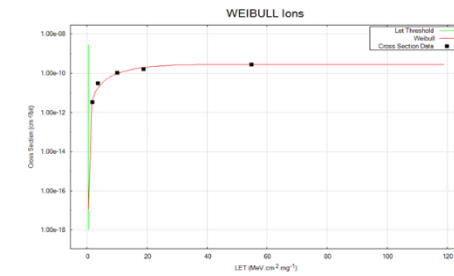
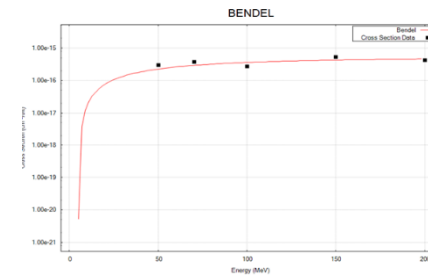
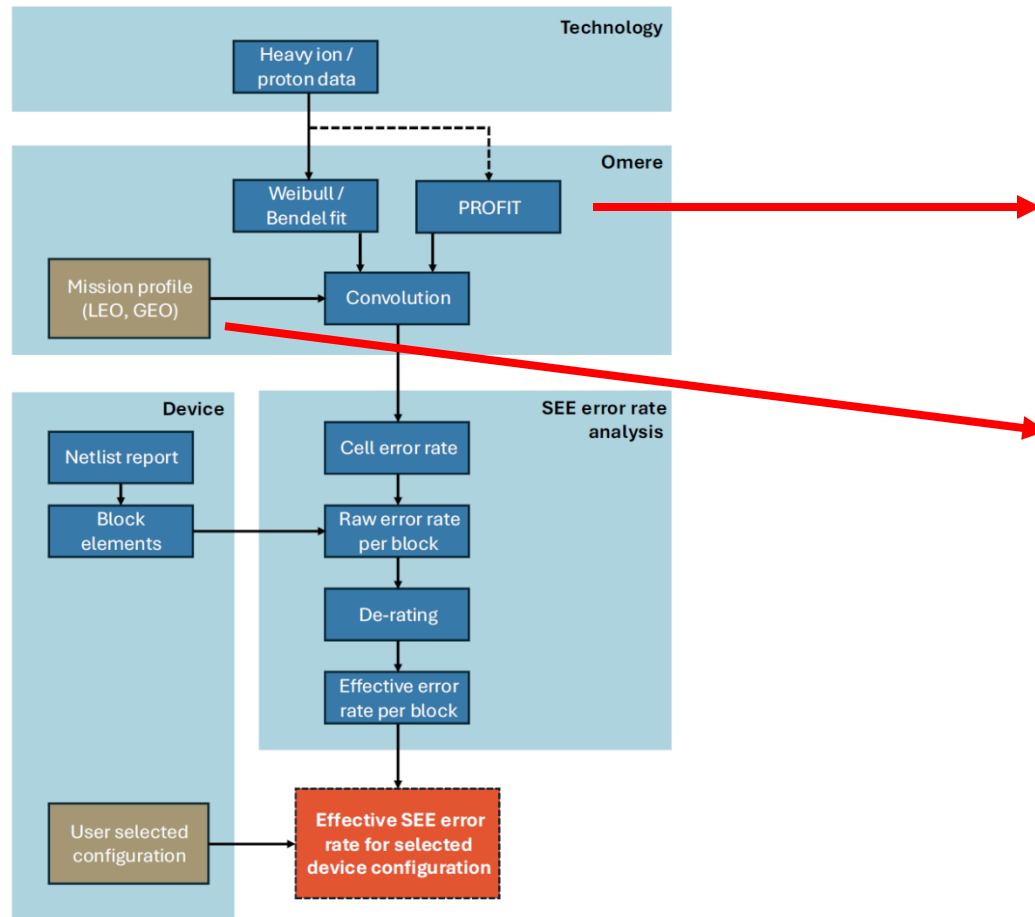


MeV	SEU
200	4.23E-16
150	5.24E-16
100	2.68E-16
70	3.73E-16
50	2.95E-16

LET	SEU
1.87	3.43E-12
3.68	2.95E-11
10.08	1.05E-10
18.84	1.59E-10
54.95	2.72E-10

Radiation hardness assurance | Analysis

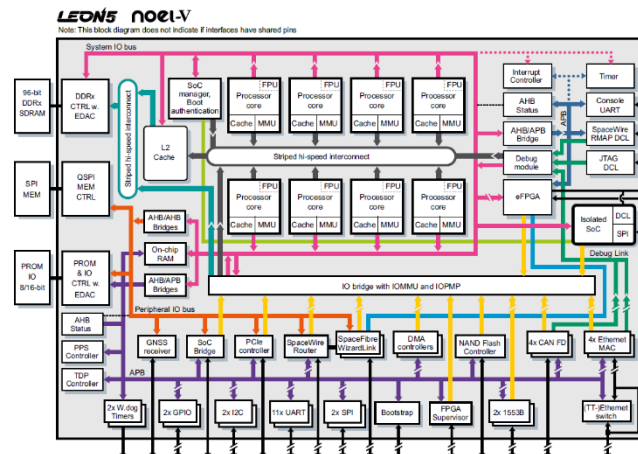
How do we estimate the radiation performance of a device during its design phase?



```

graph TD
    subgraph Technology
        A[Heavy ion / proton data]
    end
    subgraph Omere
        B[Weibull / Bendel fit]
        C[PROFIT]
        D[Convolution]
        E[Mission profile  
(LEO, GEO)]
        A --> B
        A -.-> C
        B --> D
        C --> D
        E --> D
    end
    subgraph Device
        F[Netlist report]
        G[Block elements]
    end
    subgraph SEE_error_rate_analysis
        H[Cell error rate]
        I[Raw error rate per block]
        J[De-rating]
        K[Effective error rate per block]
        L[Effective SEE error rate for selected device configuration]
    end
    D --> H
    F --> G
    G --> I
    H --> I
    I --> J
    J --> K
    K --> L
    M[User selected configuration] --> L
    style L stroke-dasharray: 5 5
  
```

Cell type	Group	List of cells in the group	Number of cells in the group	Total count of cells	Total bits/elements
RAM	ST_SPREG_BB_2048x78m4B2_aToIrmr*	ST_SPREG_BB_2048x78m4B2_aToIrmr	1	429	68530176
RAM	ST_SPREG_BB_4096x23m8B2_aToIrmr*	ST_SPREG_BB_4096x23m8B2_aToIrmr	1	133	12529664
RAM	ST_SPREG_BB_512x40m4B1_aToIrmr*	ST_SPREG_BB_512x40m4B1_aToIrmr	1	287	587760
Gate	C8T28SOL_LL_*	C8T28SOL_LL_BFX13_P4; C8T28SOL_LL_BFX24	536	5331022	5331022



Radiation hardness assurance | Analysis

How do we estimate the radiation performance of a device during its design phase?

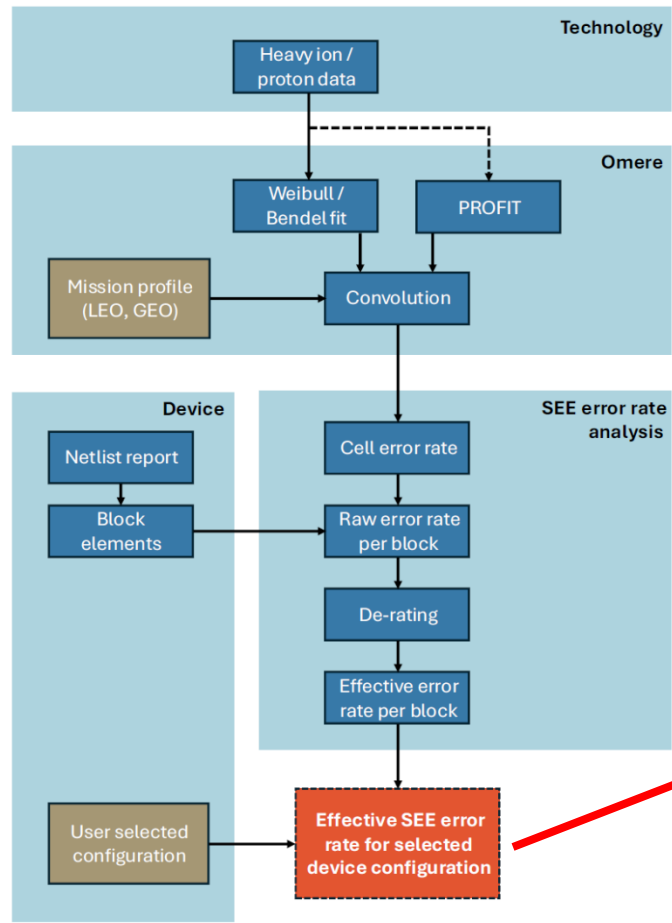


Table 6. GEO SEE error rate (error/dev/day) per GR765 block per cell group for the baseline configuration. Total and SEU effective error rates per block are also described.

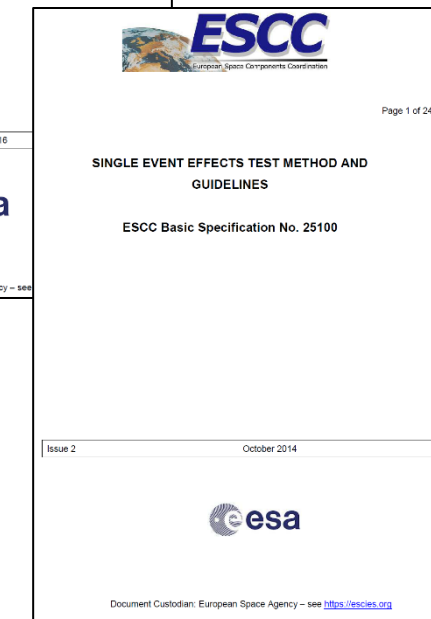
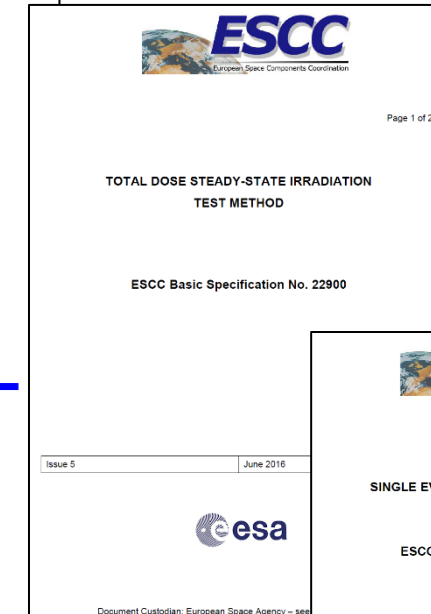
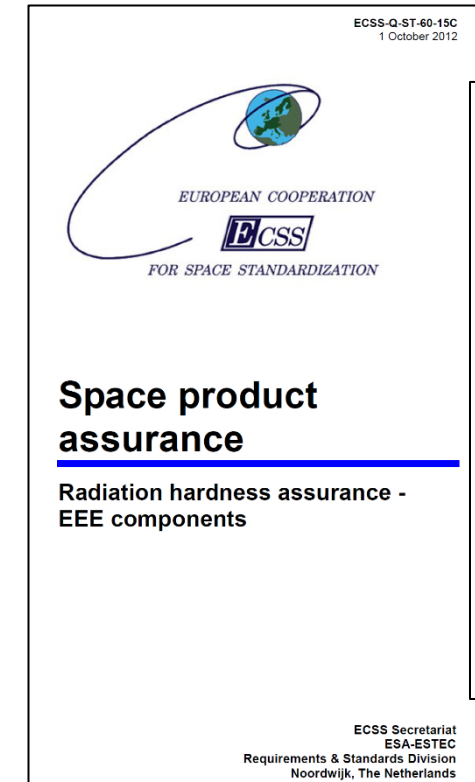
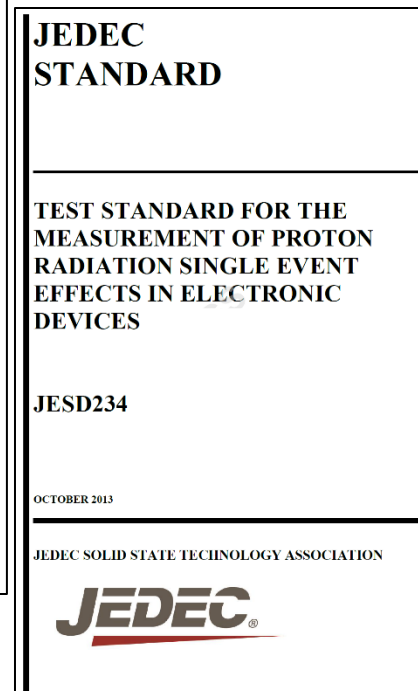
GR765 block	SRAMs	Flip-flops	Gates	PLLs	Total effective error rate	SEU effective error rate
LEON5FT_SYS	0.00E+00	1.18E-10	1.75E-08	0.00E+00	1.76E-08	1.18E-10
LEON5FT_NOELVFT_SYS	0.00E+00	6.99E-09	8.03E-07	0.00E+00	8.10E-07	6.99E-09
LEON5FT_NOELVFT_CLUS	2.13E-08	1.91E-07	4.62E-06	0.00E+00	4.83E-06	2.12E-07
LEON5FT_0	1.75E-10	1.27E-08	6.68E-07	0.00E+00	6.81E-07	1.29E-08
LEON5FT_NOELVFT_0	0.00E+00	4.98E-10	2.13E-07	0.00E+00	2.14E-07	4.98E-10
AHB	0.00E+00	1.64E-09	9.29E-08	0.00E+00	9.45E-08	1.64E-09
AHBSTAT_0	0.00E+00	1.51E-11	7.37E-10	0.00E+00	7.52E-10	1.51E-11
AHBSTAT_1	0.00E+00	1.10E-11	7.37E-10	0.00E+00	7.48E-10	1.10E-11
APB	0.00E+00	8.49E-11	1.03E-08	0.00E+00	1.03E-08	8.49E-11
UART_1	0.00E+00	5.73E-11	6.67E-09	0.00E+00	6.73E-09	5.73E-11
FTMCTRL	0.00E+00	1.07E-10	8.31E-09	0.00E+00	8.42E-09	1.07E-10
GRGPIO_0	0.00E+00	2.77E-11	3.90E-09	0.00E+00	3.93E-09	2.77E-11
GRGPIO_1	0.00E+00	2.31E-11	3.79E-09	0.00E+00	3.82E-09	2.31E-11
GRHSM	1.40E-09	1.65E-08	8.08E-07	8.33E-09	8.34E-07	1.79E-08
SOCMGR ³	1.30E-09	4.63E-09	4.71E-07	0.00E+00	4.77E-07	5.93E-09
CLOCK	0.00E+00	1.74E-10	1.11E-07	2.50E-08	1.36E-07	1.74E-10
FTADDR	0.00E+00	1.80E-08	4.75E-07	8.33E-09	5.02E-07	1.80E-08
PAD	0.00E+00	0.00E+00	1.33E-09	0.00E+00	1.33E-09	0.00E+00
GRCLKGATE	0.00E+00	1.05E-10	1.67E-09	0.00E+00	1.78E-09	1.05E-10
GRWATCHDOG	0.00E+00	3.13E-11	8.19E-10	0.00E+00	8.50E-10	3.13E-11
GPREG	0.00E+00	4.66E-12	3.59E-10	0.00E+00	3.64E-10	4.66E-12
GLOBAL	0.00E+00	0.00E+00	4.47E-07	0.00E+00	4.47E-07	0.00E+00
TOP_REMAIN	0.00E+00	1.12E-10	7.04E-09	0.00E+00	7.16E-09	1.12E-10

Table 7. LEO and GEO SEE error rates (error/dev/day) for the GR765 baseline configuration.

Environment	Total effective error rate	SEU effective error rate
LEO	2.98E-06	1.92E-07
GEO	9.09E-06	2.77E-07

Radiation hardness assurance | Testing

According to what do we test?

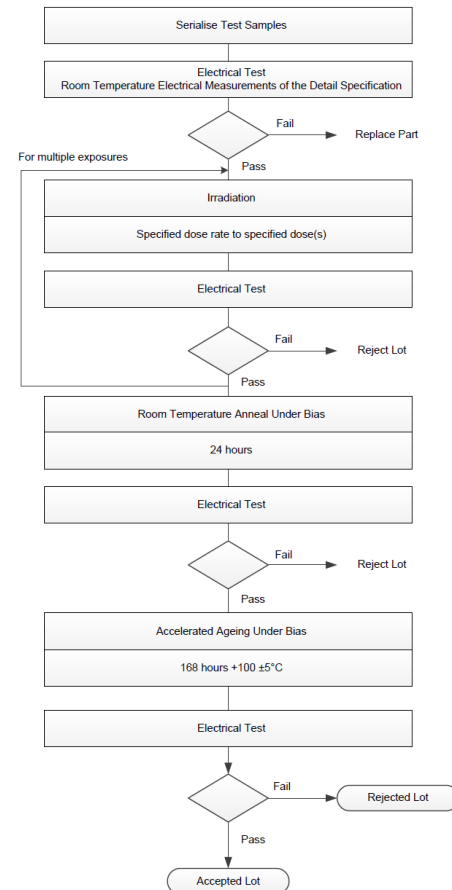


Radiation hardness assurance | Testing

How do we test?

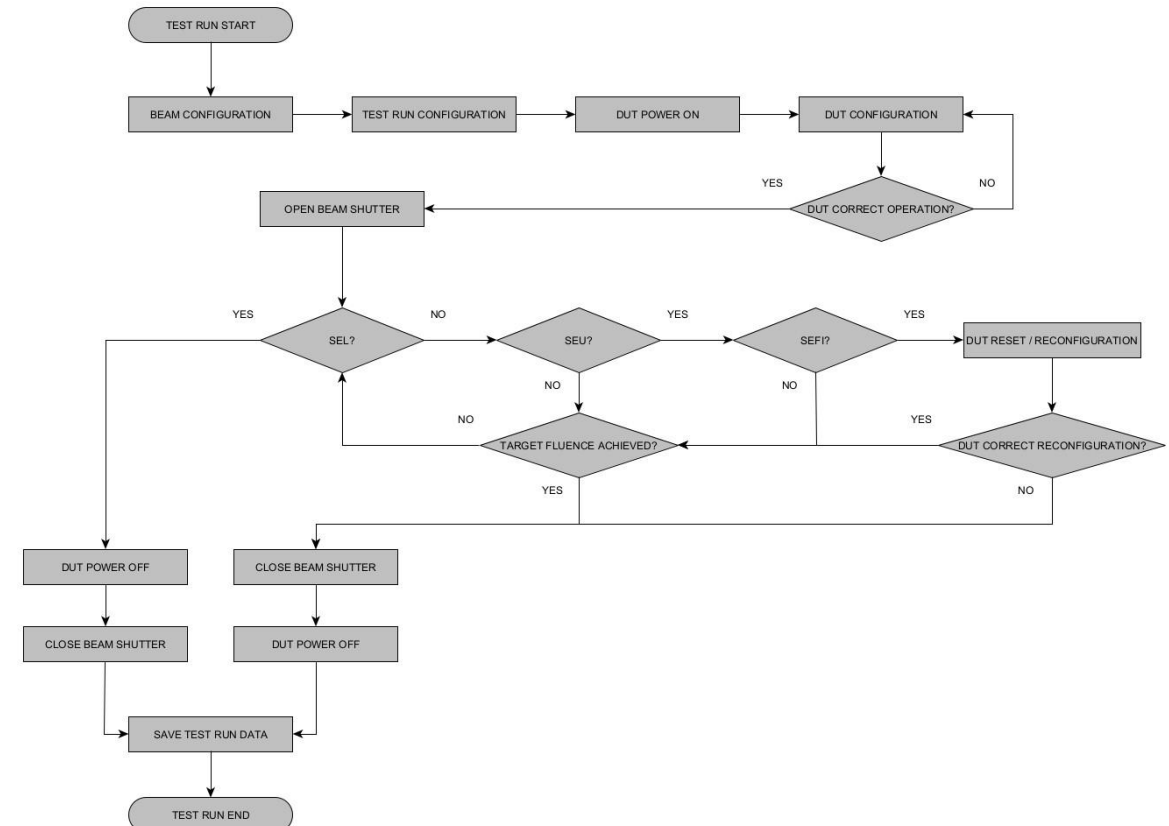
TID:

- Accumulated dose.



SEE:

- Random events.
- Test based on:
 - Target particle fluence.
 - Number of events observed.



Radiation hardness assurance | Testing

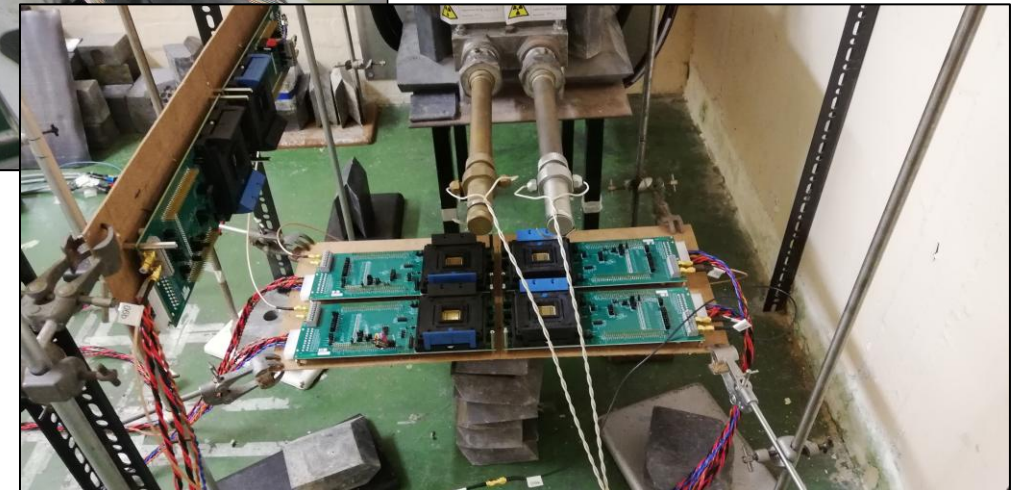
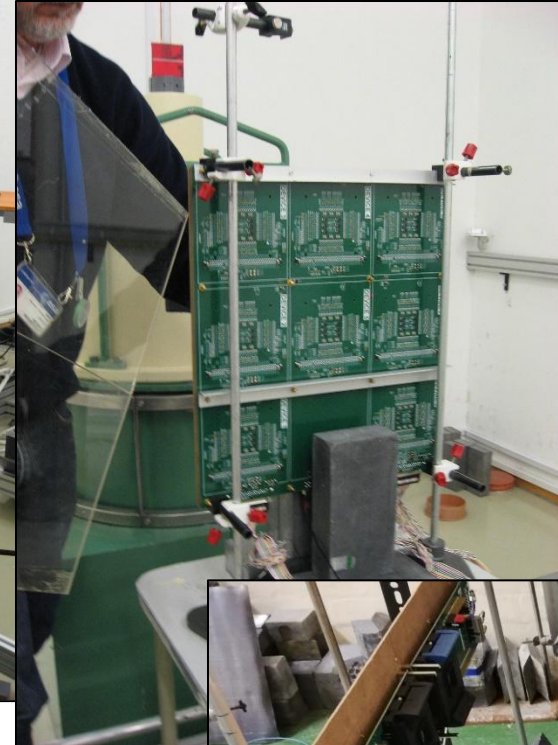
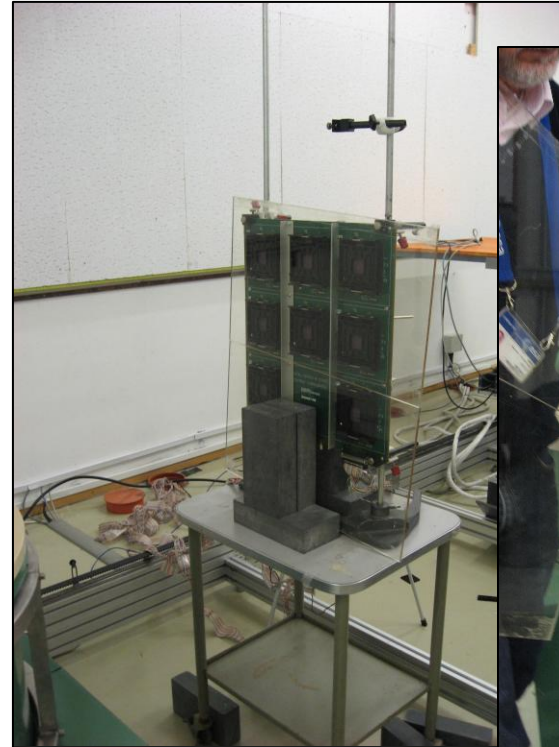
How do we test? **In practice...**



Radiation hardness assurance | Testing

How do we test? In practice...

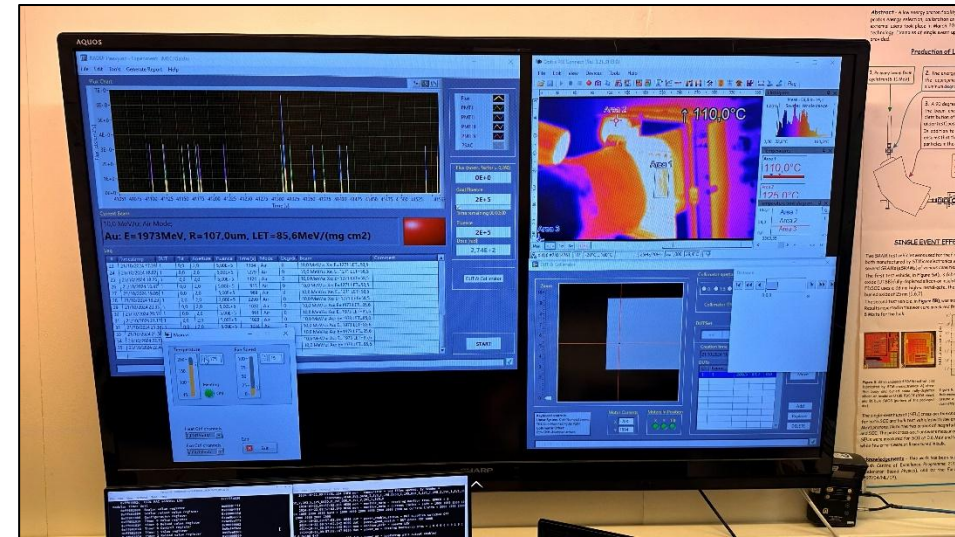
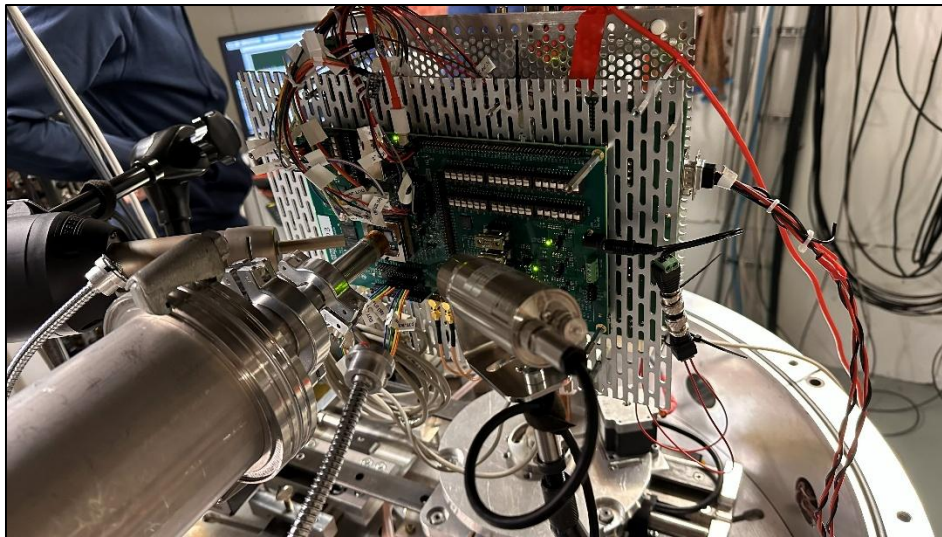
TID (Cobalt-60)



Radiation hardness assurance | Testing

How do we test? **In practice...**

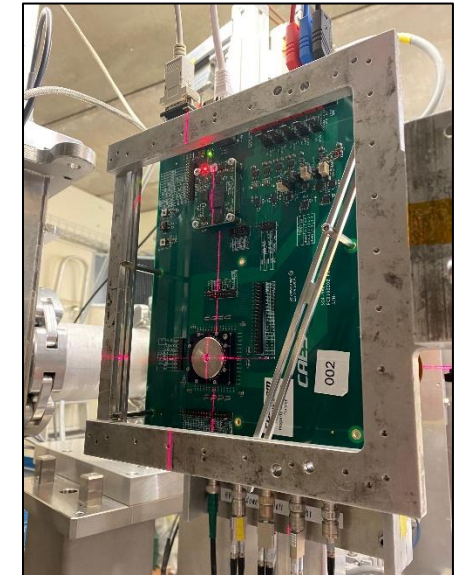
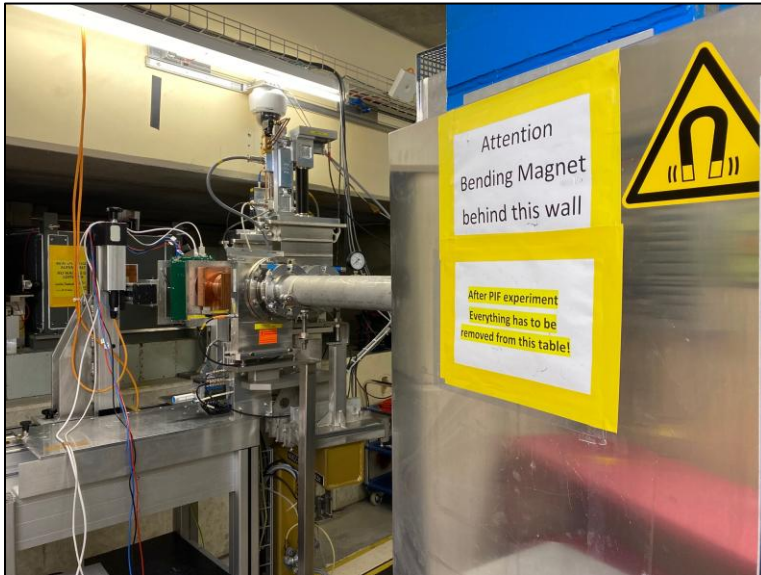
SEE (heavy ions)



Radiation hardness assurance | Testing

How do we test? **In practice...**

SEE (protons)



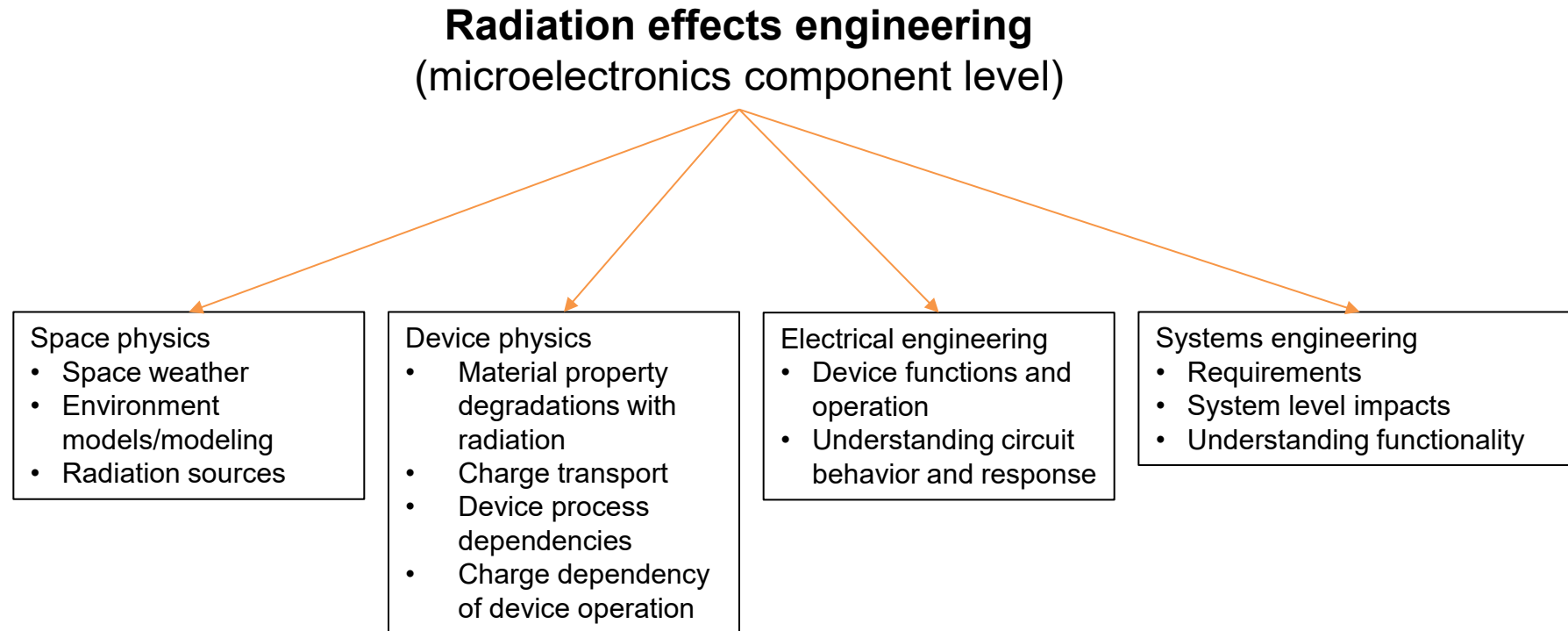
06

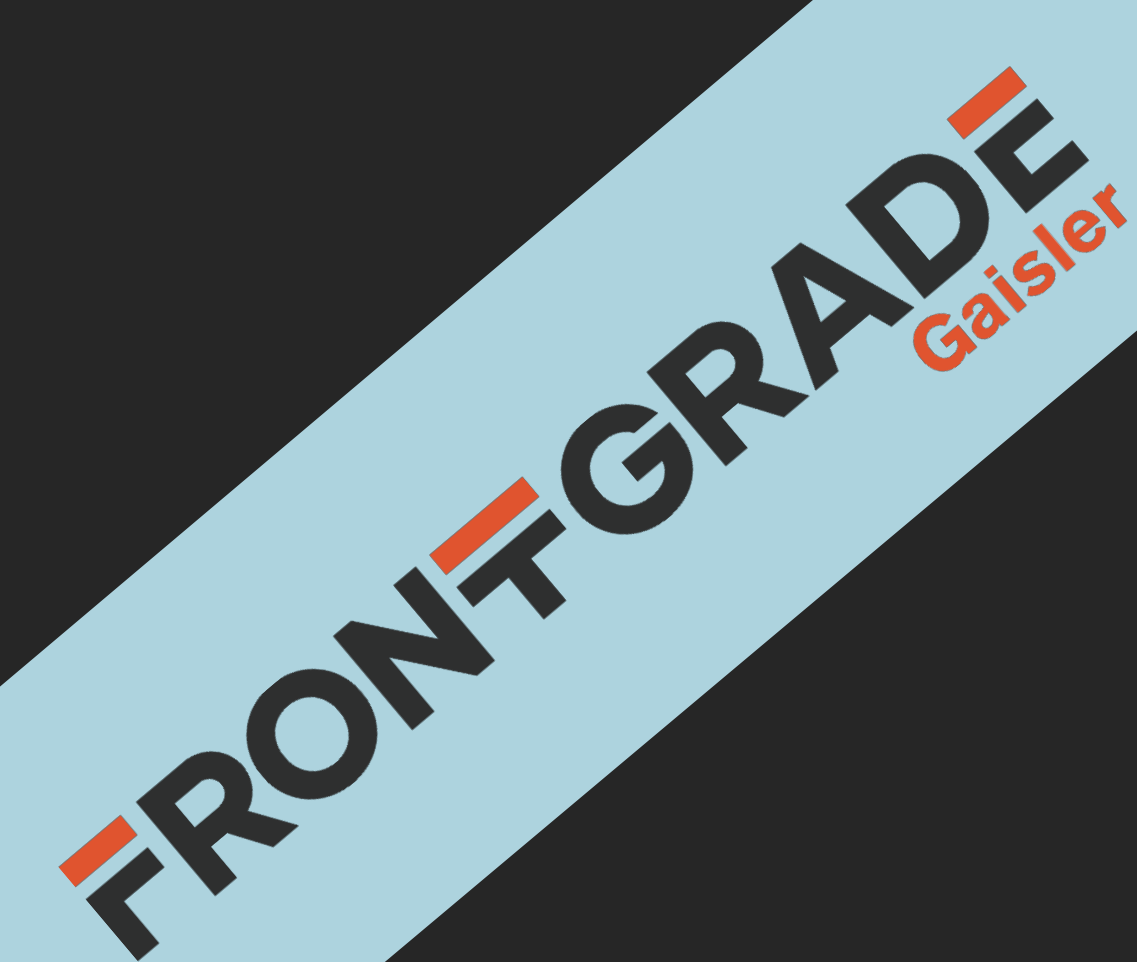


Conclusions

Conclusions

Radiation hardness assurance consists of all activities undertaken to ensure that the electronics and materials of a space system perform to their design specifications throughout exposure to the mission space environment





THANK YOU!

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